

Abdullah Sanad M Alharbi

List of Publications by Year in descending order

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Version: 2024-02-01

21
papers

422
citations

840776

11
h-index

888059

17
g-index

21
all docs

21
docs citations

21
times ranked

1025
citing authors

#	ARTICLE	IF	CITATIONS
1	Anomalous sensitivity enhancement of nano-graphitic electrochemical micro-sensors with reducing the operating voltage. <i>Biosensors and Bioelectronics</i> , 2021, 177, 112966.	10.1	4
2	Second derivative analysis and alternative data filters for multi-dimensional spectroscopies: A Fourier-space perspective. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 2020, 238, 146852.	1.7	1
3	Versatile construction of van der Waals heterostructures using a dual-function polymeric film. <i>Nature Communications</i> , 2020, 11, 3029.	12.8	41
4	Nano-engineering the material structure of preferentially oriented nano-graphitic carbon for making high-performance electrochemical micro-sensors. <i>Scientific Reports</i> , 2020, 10, 9444.	3.3	11
5	Graphene Electrodes: Quantitative Principles for Precise Engineering of Sensitivity in Graphene Electrochemical Sensors (<i>Adv. Mater.</i> 6/2019). <i>Advanced Materials</i> , 2019, 31, 1970037.	21.0	5
6	Patterning metal contacts on monolayer MoS ₂ with vanishing Schottky barriers using thermal nanolithography. <i>Nature Electronics</i> , 2019, 2, 17-25.	26.0	113
7	Quantitative Principles for Precise Engineering of Sensitivity in Graphene Electrochemical Sensors. <i>Advanced Materials</i> , 2019, 31, e1805752.	21.0	20
8	Effect of Substrate Coupling on the Performance and Variability of Monolayer MoS ₂ Transistors. <i>IEEE Electron Device Letters</i> , 2019, 40, 135-138.	3.9	11
9	Low-frequency noise in irradiated graphene FETs. <i>Applied Physics Letters</i> , 2018, 113, .	3.3	6
10	Variability in synthetic MoS_2 devices: Effect of the growth substrate. , 2018, , .		0
11	Effects of single vacancy defects on 1/f noise in graphene/b-BN FETs. , 2018, , .		0
12	Analyzing the Effect of High-k Dielectric-Mediated Doping on Contact Resistance in Top-Gated Monolayer MoS ₂ Transistors. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 4084-4092.	3.0	17
13	Material and device properties of superacid-treated monolayer molybdenum disulfide. <i>Applied Physics Letters</i> , 2017, 110, .	3.3	26
14	Optical identification using imperfections in 2D materials. <i>2D Materials</i> , 2017, 4, 045021.	4.4	24
15	Physically Unclonable Cryptographic Primitives by Chemical Vapor Deposition of Layered MoS ₂ . <i>ACS Nano</i> , 2017, 11, 12772-12779.	14.6	61
16	Experimental Study of the Detection Limit in Dual-Gate Biosensors Using Ultrathin Silicon Transistors. <i>ACS Nano</i> , 2017, 11, 7142-7147.	14.6	28
17	Hybrid CMOS-Graphene Sensor Array for Subsecond Dopamine Detection. <i>IEEE Transactions on Biomedical Circuits and Systems</i> , 2017, 11, 1192-1203.	4.0	16
18	Contact engineering of monolayer CVD MOS ₂ transistors. , 2017, , .		3

#	ARTICLE	IF	CITATIONS
19	Electronic properties of monolayer tungsten disulfide grown by chemical vapor deposition. Applied Physics Letters, 2016, 109, .	3.3	33
20	Energy band engineering of flexible gallium arsenide through substrate cracking with pre-tensioned films. Physica Status Solidi - Rapid Research Letters, 2016, 10, 627-633.	2.4	2
21	A new approach for energy band engineering in flexible GaAs devices. , 2016, , .		0